

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (currently amended): A semiconductor which consists of a compound single crystal and comprises a region (referred to as “high-defect-density region”, hereinafter) having a planar defect density of $1 \times 10^7/\text{cm}^2$ or more and a region (referred to as “low-defect-density region”, hereinafter) having a planar defect density of $1/\text{cm}^2$ or less, wherein the high-defect-density region has an electron concentration of 10 times or more of that of the low-defect-density region at room temperature.

Claim 2 (canceled)

Claim 3 (currently amended): The semiconductor according to claim 1 [[or 2]], wherein the semiconductor has a plate shape having at least one pair of opposite surfaces that are roughly parallel, on one surface (referred to as “high-defect-density surface”, hereinafter) of which, the high-defect-density region is exposed, and, on the other surface (referred to as “low-defect-density surface”, hereinafter) of which, the low-defect-density region is exposed.

Claim 4 (original): The semiconductor according to claim 1, wherein the planar defect is at least one of anti-phase boundary, stacking fault, and small-angle grain boundary.

Claim 5 (original): The semiconductor according to claim 1, wherein the compound single crystal is a group IV-IV compound single crystal, a group III-V compound single crystal, or a group II-VI compound single crystal.

Claim 6 (original): The semiconductor according to claim 1, wherein the compound single crystal is a cubic type crystal.

Claim 7 (currently amended): [[The]] A semiconductor which consists of a compound single crystal and comprises a region (referred to as “high-defect-density region”, hereinafter) having a planar defect density of $1 \times 10^7/\text{cm}^2$ or more and a region (referred to as “low-defect-density region”, hereinafter) having a planar defect density of $1/\text{cm}^2$ or less

~~according to claim 1~~, wherein the semiconductor has a transition region, between the high-defect-density region and the low-defect-density region, having a thickness of $5\ \mu\text{m}$ or less and a gradient of defect density of $4 \times 10^9/\text{cm}^3$ or more.

Claim 8 (currently amended): A semiconductor substrate, wherein a semiconductor is provided on a substrate and said semiconductor consists of a compound single crystal and comprises a region (referred to as “high-defect-density region”, hereinafter) having a planar defect density of $1 \times 10^7/\text{cm}^2$ or more and a region (referred to as “low-defect-density region”, hereinafter) having a planar defect density of $1/\text{cm}^2$ or less, wherein the high-defect-density region has an electron concentration of 10 times or more of that of the low-defect-density region at room temperature.

Claim 9 (canceled)

Claim 10 (original): The semiconductor substrate according to claim 8, wherein the semiconductor has a plate shape having at least one pair of opposite surfaces that are roughly parallel, on one surface (referred to as “high-defect-density surface”, hereinafter) of which, the high-defect-density region is exposed, and, on the other surface (referred to as “low-defect-density surface”, hereinafter) of which, the low-defect-density region is exposed.

Claim 11 (original): The semiconductor substrate according to claim 8, wherein the planar defect is at least one of anti-phase boundary, stacking fault, and small-angle grain boundary.

Claim 12 (original): The semiconductor substrate according to claim 8, wherein the compound single crystal is a group IV-IV compound single crystal, a group III-V compound single crystal, or a group II-VI compound single crystal.

Claim 13 (original): The semiconductor substrate according to claim 8, wherein the compound single crystal is a cubic type crystal.

Claim 14 (currently amended): ~~[[The]] A semiconductor substrate according to claim~~
8, wherein a semiconductor is provided on a substrate and said semiconductor consists of a
compound single crystal and comprises a region (referred to as “high-defect-density region”,
hereinafter) having a planar defect density of $1 \times 10^7/\text{cm}^2$ or more and a region (referred to as
“low-defect-density region”, hereinafter) having a planar defect density of $1/\text{cm}^2$ or less, and
the semiconductor has a transition region, between the high-defect-density region and the
low-defect-density region, having a thickness of $5 \mu\text{m}$ or less and a gradient of defect
density of $4 \times 10^9/\text{cm}^3$ or more.

Claim 15 (original): The semiconductor substrate according to claim 8, wherein the
semiconductor comprises a high-defect-density region and a low-defect-density region in this
order on a substrate.

Claim 16 (withdrawn): A method of manufacturing the semiconductor according to
claim 1 or the semiconductor substrate according to claim 8, in which a compound single
crystal is grown on a substrate using liquid phase or vapor phase, and the method comprises
the steps of;

growing a compound single crystal having a planar defect at a density of $1 \times 10^7/\text{cm}^2$
or more on the surface of the growth substrate(referred to as “step (A)”, hereinafter), and

growing a compound single crystal in an orientation differing from an orientation of
propagation of the planar defect exposed on the surface of the compound single crystal grown
in the step (A) to form a compound single crystal layer having a planar defect density of
 $1/\text{cm}^2$ or less (referred to as “step (B)”, hereinafter).

Claim 17 (withdrawn): The method according to claim 16, wherein the step (A) is
carried out by generating a planar defect at a density of $1 \times 10^7/\text{cm}^2$ or more on the surface of
the substrate as well as constantly exposing the planar defect on the surface to propagate the
structure of the planar defect.

Claim 18 (withdrawn): The method according to claim 16, wherein, following forming the compound single crystal layer having a planar defect density of $1/\text{cm}^2$ or less, the growth substrate is removed to obtain the semiconductor according to claim 1.

Claim 19 (original): A semiconductor device comprising a semiconductor, an electrode having at least one ohmic contact, and an electrode having at least one non-ohmic contact, wherein the semiconductor consists of a compound single crystal and comprises a region (referred to as "high-defect-density region", hereinafter) having a planar defect density of $1 \times 10^7/\text{cm}^2$ or more and a region (referred to as "low-defect-density region", hereinafter) having a planar defect density of $1/\text{cm}^2$ or less, and the ohmic contact is formed in the high-density defect region of the semiconductor and the non-ohmic contact is formed in the low-density defect region of the semiconductor.

Claim 20 (original): The semiconductor device according to claim 19, wherein the high-density defect region has an electron concentration of 10 times or more of that of the low-defect-density region at room temperature.

Claim 21 (original): The semiconductor device according to claim 19, wherein the semiconductor has a plate shape having at least one pair of opposite surfaces that are roughly parallel, on one surface (referred to as "high-defect-density surface", hereinafter) of which, the high-defect-density region is exposed, and, on the other surface (referred to as "low-defect-density surface", hereinafter) of which, the low-defect-density region is exposed.

Claim 22 (original): The semiconductor device according to claim 19, wherein the planar defect is at least one of anti-phase boundary, stacking fault, and small-angle grain boundary.

Claim 23 (original): The semiconductor device according to claim 19, wherein the compound single crystal is a group IV-IV compound single crystal, a group III-V compound single crystal, or a group II-VI compound single crystal.

Claim 24 (original): The semiconductor device according to claim 19, wherein the compound single crystal is a cubic type crystal.

Claim 25 (original): The semiconductor device according to claim 19, wherein the semiconductor has a transition region, between the high-defect-density region and the low-defect-density region, having a thickness of $5\ \mu\text{m}$ or less and a gradient of defect density of $4 \times 10^9/\text{cm}^3$ or more.